

Title (en)

Method of producing low resistance contacts.

Title (de)

Verfahren zum Herstellen von Kontakten mit niedrigem Widerstand.

Title (fr)

Méthode de fabrication de contacts à faible résistance.

Publication

EP 0486244 A1 19920520 (EN)

Application

EP 91310398 A 19911111

Priority

US 61463590 A 19901116

Abstract (en)

The method for fabrication of low resistance semiconductor contacts includes depositing an insulating layer (14) over the integrated circuit. An adhesion layer (16) is then formed over the insulating layer. A contact opening (18) is formed through the adhesion layer and the insulating layer. A metal silicide layer (20) is then deposited over the integrated circuit including the contact opening. The metal silicide layer and adhesion layer are then etched to form interconnections. <IMAGE>

IPC 1-7

H01L 21/285; **H01L 21/60**; **H01L 21/90**

IPC 8 full level

H01L 21/28 (2006.01); **H01L 21/3205** (2006.01); **H01L 21/768** (2006.01); **H01L 23/532** (2006.01)

CPC (source: EP KR)

H01L 21/28 (2013.01 - KR); **H01L 21/76838** (2013.01 - EP); **H01L 23/53271** (2013.01 - EP); **H01L 23/5329** (2013.01 - EP); **H01L 23/53295** (2013.01 - EP); **H01L 2924/0002** (2013.01 - EP)

Citation (search report)

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DE FR GB IT

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